

**Appendix**

Changes to the current claims.

Please cancel claim 20 and amend claims 1, 12, and 21 as follows:

1. (Amended) A method of forming a semiconductor structure, comprising:  
forming an isolation region in a semiconductor substrate; wherein  
a first oxide layer is on said substrate,  
a first sacrificial layer is on said first oxide layer, wherein said first  
sacrificial layer comprises an oxide, and  
a first nitride layer is on said first sacrificial layer.
12. (Amended) A method of forming a semiconductor structure, comprising:  
removing a first nitride layer and a first sacrificial layer, wherein said first  
sacrificial layer comprises an oxide;  
wherein a first oxide layer is on a substrate,  
said first sacrificial layer is on said first oxide layer, and  
said first nitride layer is on said first sacrificial layer.
- ~~20. In a method of forming an isolation region in a semiconductor device,  
including forming an isolation nitride on a substrate, the improvement comprising  
forming a first sacrificial layer between said isolation nitride and said substrate.~~
21. (Amended) In a method of forming an isolation region in a  
semiconductor device, including forming an isolation nitride on a substrate, the  
improvement comprising forming a first sacrificial layer between said isolation nitride  
and said substrate and~~The method of claim 20, further comprising forming a second  
sacrificial layer between said first sacrificial layer and said substrate.~~